

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-25 (Canceled).

26. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin film transistor comprising:

a gate electrode formed over the substrate, ~~the gate electrode comprising aluminum;~~

a first insulating layer, wherein a first portion of said first insulating layer is formed over said gate electrode;

a channel formation region formed in a first semiconductor layer;

source and drain regions, each of the source and drain regions comprising a second semiconductor layer including impurities, formed over the first semiconductor layer;

a second insulating layer comprising an inorganic material and formed over the first semiconductor layer and the second semiconductor layer containing the impurities so as to be in contact with at least a part of the channel formation region;

a pixel electrode over the first insulating layer, ~~the pixel electrode comprising indium, zinc and oxygen;~~

a source wiring formed over the source region;

a drain wiring formed over the drain region and overlapping with a first portion of the pixel electrode;

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a second portion of the first insulating layer over the storage capacitor wiring and a second portion of the pixel electrode; and

an input terminal portion formed along an end portion of the substrate and electrically connected to the source wiring,

wherein the input terminal portion comprises a first layer comprising the same material as the gate electrode and a second layer comprising the same material as the pixel electrode,

wherein the source wiring is electrically connected to the second layer of said input terminal portion,

wherein the storage capacitor wiring is covered by the pixel electrode, [[and]]

wherein the second insulating layer overlaps with a third portion of the pixel electrode,

wherein the first semiconductor layer comprises a first portion between the source and drain regions and a second portion below the source and drain regions,

wherein the first portion of the first semiconductor layer overlaps with the gate electrode, and

wherein a film thickness of the first portion of the first semiconductor layer is thinner than that of the second portion of the first semiconductor layer.

27. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin film transistor comprising:

a gate electrode formed over the substrate, ~~the gate electrode comprising aluminum;~~

a first insulating layer, wherein a first portion of said first insulating layer is formed over said

gate electrode;

a channel formation region formed in a first semiconductor layer;

source and drain regions, each of the source and drain regions comprising a second semiconductor layer including impurities, formed over the first semiconductor layer;

a second insulating layer comprising an inorganic material and formed over the first semiconductor layer and the second semiconductor layer containing the impurities so as to be in contact with at least a part of the channel formation region;

a pixel electrode formed in contact with the first insulating layer, ~~the pixel electrode comprising indium, zinc and oxygen;~~

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a second portion of the first insulating layer over the storage capacitor wiring and a portion of the pixel electrode; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a first wiring,

wherein the input terminal portion comprises a first layer comprising the same material as the gate electrode and a second layer comprising the same material as the pixel electrode in contact with the first layer through a contact hole formed only in the first insulating layer,

wherein a portion of the first wiring is formed over the second layer of said input terminal portion, [[and]]

wherein the storage capacitor wiring is covered by the pixel electrode,

wherein the first semiconductor layer comprises a first portion between the source and drain regions and a second portion below the source and drain regions,

wherein the first portion of the first semiconductor layer overlaps with the gate electrode, and
wherein a film thickness of the first portion of the first semiconductor layer is thinner than that of the
second portion of the first semiconductor layer.

28. (Currently Amended) A semiconductor device comprising:

- a substrate having an insulating surface;
- a thin film transistor formed over the substrate, the thin film transistor comprising:
 - a gate electrode formed over the substrate, ~~the gate electrode comprising aluminum;~~
 - a first insulating layer, wherein a first portion of said first insulating layer is formed over said gate electrode;
 - a channel formation region formed in a first semiconductor layer;
 - source and drain regions, each of the source and drain regions comprising a second semiconductor layer including impurities of first conductivity type, formed over the first semiconductor layer;
 - a pixel electrode over the first insulating layer, ~~the pixel electrode comprising indium, zinc and oxygen;~~
 - a second insulating layer comprising an inorganic material and overlapping with a first portion of the pixel electrode, the first semiconductor layer and the second semiconductor layer containing the impurities of first conductivity type so as to be in contact with at least a part of the channel formation region;
 - a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a second portion of the first insulating layer over the storage capacitor

wiring and a second portion of the pixel electrode; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a first wiring,

wherein the input terminal portion comprises a first layer comprising the same material as the gate electrode and a second layer comprising the same material as the pixel electrode, and

wherein the first wiring is electrically connected to the second layer of said input terminal portion,

wherein each of the gate electrode, the storage capacitor wiring and the first layer has a tapered portion, [[and]]

wherein the storage capacitor wiring is covered by the pixel electrode,

wherein the first semiconductor layer comprises a first portion between the source and drain regions and a second portion below the source and drain regions,

wherein the first portion of the first semiconductor layer overlaps with the gate electrode, and

wherein a film thickness of the first portion of the first semiconductor layer is thinner than that of the second portion of the first semiconductor layer.

29. (Canceled)

30. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin film transistor comprising:

a gate electrode formed over the substrate, ~~the gate electrode comprising aluminum;~~

a first insulating layer, wherein a first portion of said first insulating layer is formed over said gate electrode;

a channel formation region formed in a first semiconductor layer;

source and drain regions, each of the source and drain regions comprising a second semiconductor layer including impurities, formed over the first semiconductor layer;

a second insulating layer comprising an inorganic material and formed over the first semiconductor layer and the second semiconductor layer containing the impurities so as to be in contact with at least a part of the channel formation region;

a pixel electrode formed in contact with the first insulating layer, ~~the pixel electrode comprising indium, zinc and oxygen;~~

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a second portion of the first insulating layer over the storage capacitor wiring and the pixel electrode; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a first wiring,

wherein the input terminal portion comprises a first layer comprising the same material as the gate electrode and a second layer comprising the same material as the pixel electrode in contact with the first layer through a contact hole formed only in the first insulating layer,

wherein a portion of the first wiring is formed over the second layer of said input terminal portion,

wherein each of the gate electrode, the storage capacitor wiring and the first layer has a tapered portion, [[and]]

wherein the storage capacitor wiring is covered by the pixel electrode,
wherein the first semiconductor layer comprises a first portion between the source and drain regions and a second portion below the source and drain regions,
wherein the first portion of the first semiconductor layer overlaps with the gate electrode, and
wherein a film thickness of the first portion of the first semiconductor layer is thinner than that of the second portion of the first semiconductor layer.

31. (Currently Amended) A semiconductor device comprising:
a substrate having an insulating surface;
a thin film transistor formed over the substrate, the thin film transistor comprising:
a gate electrode formed over the substrate, ~~the gate electrode comprising aluminum;~~
a first insulating layer, wherein a first portion of said first insulating layer is formed over said gate electrode;
a channel formation region formed in a first semiconductor layer;
source and drain regions, each of the source and drain regions comprising a second semiconductor layer including impurities, formed over the first semiconductor layer;
a second insulating layer comprising an inorganic material and formed over the first semiconductor layer and the second semiconductor layer containing the impurities so as to be in contact with at least a part of the channel formation region;
a pixel electrode over the first insulating layer, ~~the pixel electrode comprising indium, zinc and oxygen;~~
a source wiring formed over the source region;

a drain wiring formed over the drain region and overlapping with a first portion of the pixel electrode;

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a second portion of the first insulating layer over the storage capacitor wiring and a second portion of the pixel electrode; and

an input terminal portion formed along an end portion of the substrate and electrically connected to the source wiring,

wherein the input terminal portion comprises a first layer comprising the same material as the gate electrode and a second layer comprising the same material as the pixel electrode,

wherein the source wiring is electrically connected to the second layer of said input terminal portion, [[and]]

wherein the second insulating layer overlaps with a third portion of the pixel electrode,

wherein the first semiconductor layer comprises a first portion between the source and drain regions and a second portion below the source and drain regions,

wherein the first portion of the first semiconductor layer overlaps with the gate electrode, and

wherein a film thickness of the first portion of the first semiconductor layer is thinner than that of the second portion of the first semiconductor layer.

32. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin film transistor comprising:

a gate electrode formed over the substrate, ~~the gate electrode comprising aluminum;~~

a first insulating layer, wherein a first portion of said first insulating layer is formed over said gate electrode;

a channel formation region formed in a first semiconductor layer;

source and drain regions, each of the source and drain regions comprising a second semiconductor layer including impurities, formed over the first semiconductor layer;

a second insulating layer comprising an inorganic material and formed over the first semiconductor layer and the second semiconductor layer containing the impurities so as to be in contact with at least a part of the channel formation region;

a pixel electrode formed in contact with the first insulating layer, ~~the pixel electrode comprising indium, zinc and oxygen;~~

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a second portion of the first insulating layer over the storage capacitor wiring and a portion of the pixel electrode; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a first wiring,

wherein the input terminal portion comprises a first layer comprising the same material as the gate electrode and a second layer comprising the same material as the pixel electrode in contact with the first layer through a contact hole formed only in the first insulating layer, [[and]]

wherein a portion of the first wiring is formed over the second layer of said input terminal portion,

wherein the first semiconductor layer comprises a first portion between the source and drain regions and a second portion below the source and drain regions.

wherein the first portion of the first semiconductor layer overlaps with the gate electrode, and
wherein a film thickness of the first portion of the first semiconductor layer is thinner than that of the
second portion of the first semiconductor layer.

33. (Currently Amended) A semiconductor device comprising:

- a substrate having an insulating surface;
- a thin film transistor formed over the substrate, the thin film transistor comprising:
 - a gate electrode formed over the substrate, ~~the gate electrode comprising aluminum;~~
 - a first insulating layer, wherein a first portion of said first insulating layer is formed over said gate electrode;
 - a channel formation region formed in a first semiconductor layer;
 - source and drain regions, each of the source and drain regions comprising a second semiconductor layer including impurities of, formed over the first semiconductor layer;
 - a pixel electrode over the first insulating layer, ~~the pixel electrode comprising indium, zinc and oxygen;~~
 - a second insulating layer comprising an inorganic material and overlapping with a first portion of the pixel electrode, the first semiconductor layer and the second semiconductor layer containing the impurities so as to be in contact with at least a part of the channel formation region;
 - a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a second portion of the first insulating layer over the storage capacitor wiring and a second portion of the pixel electrode; and
 - an input terminal portion formed along an end portion of the substrate and electrically

connected to a first wiring,

wherein the input terminal portion comprises a first layer comprising the same material as the gate electrode and a second layer comprising the same material as the pixel electrode,

wherein the first wiring is electrically connected to the second layer of said input terminal portion, [[and]]

wherein each of the gate electrode, the storage capacitor wiring and the first layer has a tapered portion,

wherein the first semiconductor layer comprises a first portion between the source and drain regions and a second portion below the source and drain regions,

wherein the first portion of the first semiconductor layer overlaps with the gate electrode, and

wherein a film thickness of the first portion of the first semiconductor layer is thinner than that of the second portion of the first semiconductor layer.

34. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin film transistor comprising:

a gate electrode formed over the substrate, ~~the gate electrode comprising aluminum;~~

a first insulating layer, wherein a first portion of said first insulating layer is formed over said gate electrode;

a channel formation region formed in a first semiconductor layer;

source and drain regions, each of the source and drain regions comprising a second semiconductor layer including impurities, formed over the first semiconductor layer;

a second insulating layer comprising an inorganic material and formed over the first semiconductor layer and the second semiconductor layer containing the impurities so as to be in contact with at least a part of the channel formation region;

a pixel electrode formed in contact with the first insulating layer, ~~the pixel electrode comprising indium, zinc and oxygen;~~

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a second portion of the first insulating layer over the storage capacitor wiring and the pixel electrode; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a first wiring,

wherein the input terminal portion comprises a first layer comprising the same material as the gate electrode and a second layer comprising the same material as the pixel electrode in contact with the first layer through a contact hole formed only in the first insulating layer,

wherein a portion of the first wiring is formed over the second layer of said input terminal portion, [[and]]

wherein each of the gate electrode, the storage capacitor wiring and the first layer has a tapered portion,

wherein the first semiconductor layer comprises a first portion between the source and drain regions and a second portion below the source and drain regions,

wherein the first portion of the first semiconductor layer overlaps with the gate electrode, and

wherein a film thickness of the first portion of the first semiconductor layer is thinner than that of the second portion of the first semiconductor layer.

35. (Previously presented) A semiconductor device according to claim 26, wherein the semiconductor device is selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic play device and a television.

36. (Previously presented) A semiconductor device according to claim 27, wherein the semiconductor device is selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic play device and a television.

37. (Previously presented) A semiconductor device according to claim 28, wherein the semiconductor device is selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic play device and a television.

38. (Previously presented) A semiconductor device according to claim 30, wherein the semiconductor device is selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic play device and a television.

39. (Previously presented) A semiconductor device according to claim 31, wherein the semiconductor device is selected from a group consisting of a personal computer, a video camera, a

portable information terminal, a digital camera, a digital video disc player, an electronic play device and a television.

40. (Previously presented) A semiconductor device according to claim 32, wherein the semiconductor device is selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic play device and a television.

41. (Previously presented) A semiconductor device according to claim 33, wherein the semiconductor device is selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic play device and a television.

42. (Previously presented) A semiconductor device according to claim 34, wherein the semiconductor device is selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic play device and a television.

43. (Currently Amended) A semiconductor device according to claim 26, wherein the source wiring is completely covered by the second insulating layer.

44. (Currently Amended) A semiconductor device according to claim 27, wherein the first

wiring is ~~completely~~ covered by the second insulating layer.

45. (Currently Amended) A semiconductor device according to claim 28, wherein the first wiring is ~~completely~~ covered by the second insulating layer.

46. (Currently Amended) A semiconductor device according to claim 30, wherein the first wiring is ~~completely~~ covered by the second insulating layer.

47. (Currently Amended) A semiconductor device according to claim 31, wherein the source wiring is ~~completely~~ covered by the second insulating layer.

48. (Currently Amended) A semiconductor device according to claim 32, wherein the first wiring is ~~completely~~ covered by the second insulating layer.

49. (Currently Amended) A semiconductor device according to claim 33, wherein the first wiring is ~~completely~~ covered by the second insulating layer.

50. (Currently Amended) A semiconductor device according to claim 34, wherein the first wiring is ~~completely~~ covered by the second insulating layer.

51-66. (Canceled)

67. (New) A semiconductor device according to claim 26, wherein the gate electrode comprises aluminum and the pixel electrode comprises indium, zinc and oxygen.

68. (New) A semiconductor device according to claim 27, wherein the gate electrode comprises aluminum and the pixel electrode comprises indium, zinc and oxygen.

69. (New) A semiconductor device according to claim 28, wherein the gate electrode comprises aluminum and the pixel electrode comprises indium, zinc and oxygen.

70. (New) A semiconductor device according to claim 30, wherein the gate electrode comprises aluminum and the pixel electrode comprises indium, zinc and oxygen.

71. (New) A semiconductor device according to claim 31, wherein the gate electrode comprises aluminum and the pixel electrode comprises indium, zinc and oxygen.

72. (New) A semiconductor device according to claim 32, wherein the gate electrode comprises aluminum and the pixel electrode comprises indium, zinc and oxygen.

73. (New) A semiconductor device according to claim 33, wherein the gate electrode comprises aluminum and the pixel electrode comprises indium, zinc and oxygen.

74. (New) A semiconductor device according to claim 34, wherein the gate electrode

comprises aluminum and the pixel electrode comprises indium, zinc and oxygen.

75. (New) A semiconductor device according to claim 26, wherein the semiconductor device is a liquid crystal display device.

76. (New) A semiconductor device according to claim 27, wherein the semiconductor device is a liquid crystal display device.

77. (New) A semiconductor device according to claim 28, wherein the semiconductor device is a liquid crystal display device.

78. (New) A semiconductor device according to claim 30, wherein the semiconductor device is a liquid crystal display device.

79. (New) A semiconductor device according to claim 31, wherein the semiconductor device is a liquid crystal display device.

80. (New) A semiconductor device according to claim 32, wherein the semiconductor device is a liquid crystal display device.

81. (New) A semiconductor device according to claim 33, wherein the semiconductor device is a liquid crystal display device.

82. (New) A semiconductor device according to claim 34, wherein the semiconductor device is a liquid crystal display device.

83. (New) A semiconductor device according to claim 28, wherein an angle of the taper portion is 1° to 20° .

84. (New) A semiconductor device according to claim 30, wherein an angle of the taper portion is 1° to 20° .

85. (New) A semiconductor device according to claim 33, wherein an angle of the taper portion is 1° to 20° .

86. (New) A semiconductor device according to claim 34, wherein an angle of the taper portion is 1° to 20° .

87. (New) A semiconductor device according to claim 26, wherein the first semiconductor layer comprises a micro-crystal semiconductor.

88. (New) A semiconductor device according to claim 27, wherein the first semiconductor layer comprises a micro-crystal semiconductor.

89. (New) A semiconductor device according to claim 28, wherein the first semiconductor

layer comprises a micro-crystal semiconductor.

90. (New) A semiconductor device according to claim 30, wherein the first semiconductor layer comprises a micro-crystal semiconductor.

91. (New) A semiconductor device according to claim 31, wherein the first semiconductor layer comprises a micro-crystal semiconductor.

92. (New) A semiconductor device according to claim 32, wherein the first semiconductor layer comprises a micro-crystal semiconductor.

93. (New) A semiconductor device according to claim 33, wherein the first semiconductor layer comprises a micro-crystal semiconductor.

94. (New) A semiconductor device according to claim 34, wherein the first semiconductor layer comprises a micro-crystal semiconductor.